

**IN THE CLAIMS**

Cancel claims 1-15 without prejudice or disclaimer; and add new claims 16-21 as set forth below:

16. (New) A method of manufacturing an electron device, comprising steps of:

preparing a substrate on which a photoresist film is formed;

preparing a mask, the mask providing a first and second phase shift pattern area on a mask plate,

wherein the first phase shift pattern area contains a plurality of apertures formed in a resist light shielding area, and the second phase shift pattern area contains the same pattern with the first phase shift pattern,

wherein a phase of the second phase shift pattern area is mutually inverse to that of the first phase shift area;

transferring a pattern formed in the first phase shift pattern area onto a photoresist film formed on the substrate; and

transferring a pattern formed in the second phase shift pattern area onto the photoresist film formed on the substrate in such a way that a pattern formed in the first phase shift pattern area is overlapped with a pattern formed in the first phase shift pattern area which is transferred onto a photoresist film formed on the substrate.

17. (New) A method of manufacturing an electron device according to claim 16, wherein:

the plurality of apertures contain repeated linear patterns which is transferred onto the substrate.

18. (New) A method of manufacturing an electron device according to claim 16, wherein:

the plurality of apertures are contained in isolated patterns which are transferred onto the substrate and in adjacent areas thereto, and auxiliary patterns which are not transferred onto the substrate are contained.

19. (New) A method of manufacturing an electron device according to claim 16, wherein :

the first phase shift pattern area and the second phase shift pattern area are transferred onto the photoresist film formed on the substrate by using a scanner.

20. (New) A method of manufacturing a semiconductor device, comprising steps of:

preparing a semiconductor substrate on which a photoresist film is formed,

preparing a first and second phase shift mask, the first phase shift mask providing a first and second apertures formed in a resist light shielding area in which phases of an exposure light passing through the first and second apertures are inverse respectively, and

the second phase shift mask providing a third and fourth apertures in which the third and fourth apertures are the same patterns with the first and second apertures,

wherein phases of the third and fourth apertures are mutually inverse to those of the first and second phase apertures;

transferring the first and second apertures formed in the first phase shift patterns area onto a photoresist film formed on the semiconductor substrate; and

transferring the third and fourth apertures onto the photoresist film formed on the semiconductor substrate in such a way that the third and fourth apertures formed in the second phase shift pattern area are overlapped with the first and second apertures formed on the first phase shift pattern area being transferred onto a photoresist film formed on the semiconductor substrate.

21. (New) A method of manufacturing a semiconductor device according to claim 20, wherein:

the first phase shift mask and the second phase shift mask are formed on the same mask plate.